

`mos_bsim1_p.ece`

Description

`mos_bsim1_p.ece` is a BSIM1 model for a p -channel MOS transistor. The real parameters have the same meaning as in the BSIM1 model implemented in SPICE 3.

The source, drain, gate, and bulk currents are made available as output variables `i1`, `i2`, `igate`, and `ibulk`, respectively. The power absorbed by the transistor is made available as `pwr_elec`.

AC (small-signal) implementation of the model is also incorporated, following SPICE 3.